TOSHIBA INTELLIGENT POWER MODULE SILICON N CHANNEL IGBT

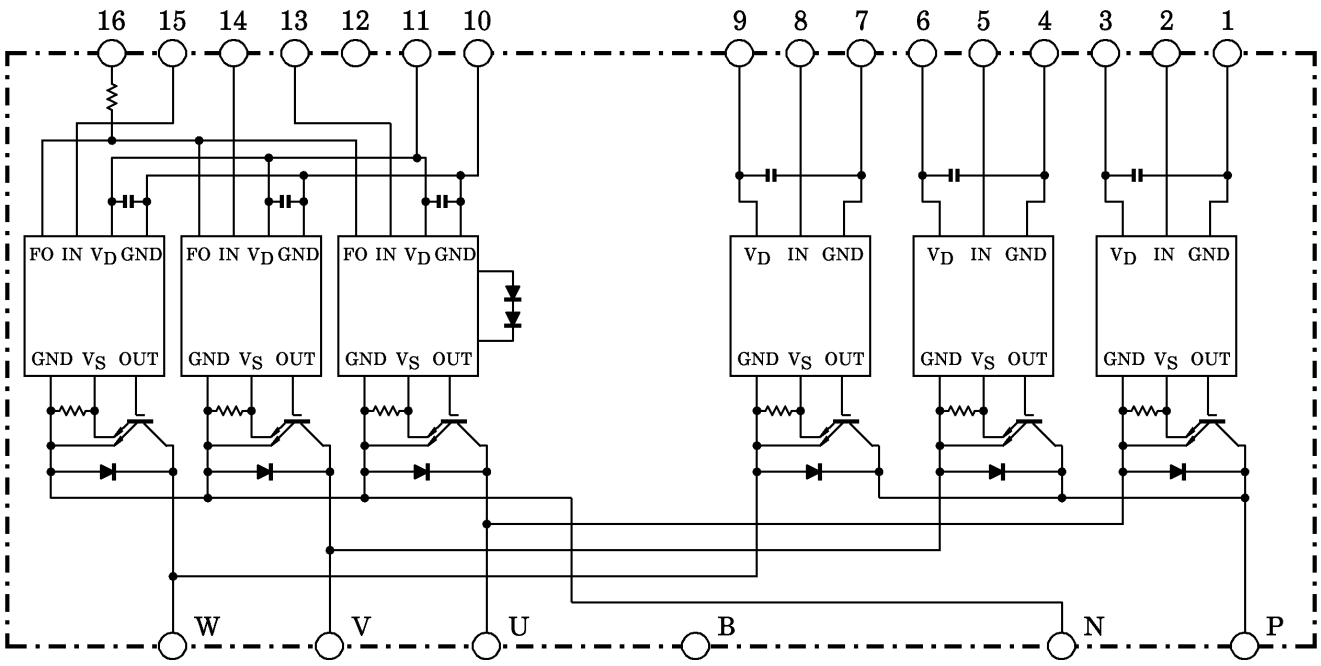
MIG75J101H

HIGH POWER SWITCHING APPLICATIONS

MOTOR CONTROL APPLICATIONS

- Integrates Inverter & Control Circuits (IGBT drive units, Protection units for Over-Current, Under-Voltage & Over-Temperature) in One Package.
- The Electrodes are Isolated from Case.
- High Speed Type IGBT : $V_{CE\ (sat)}$ = 2.5 V (Max.)
  t_{off} = 3.0 μs (Max.)
  t_{rr} = 0.30 μs (Max.)
- Outline : TOSHIBA 2-110A1A
- Weight : 520 g

EQUIVALENT CIRCUIT



1. GND (U)	2. IN (U)	3. V_D (U)	4. GND (V)	5. IN (V)	6. V_D (V)
7. GND (W)	8. IN (W)	9. V_D (W)	10.GND (L)	11.V_D (L)	12.OPEN
13.IN (X)	14.IN (Y)	15.IN (Z)	16.FO		

961001EAA1

MAXIMUM RATINGS (T_j = 25°C)

STAGE	CHARACTERISTIC	CONDITION	SYMBOL	RATINGS	UNIT
Inverter	Supply Voltage	P-N power terminal	V_{CC}	450	V
	Collector-Emitter Voltage	—	V_{CES}	600	V
	Collector Current	Tc = 25°C, DC	I_C	75	A
	Forward Current	Tc = 25°C, DC	I_F	75	A
	Collector Power Dissipation	Tc = 25°C	P_C	235	W
	Junction Temperature	—	T_j	150	°C
Control	Control Supply Voltage	V_D-GND terminal	V_D	20	V
	Input Voltage	IN-GND terminal	V_{IN}	20	V
	Fault Output Voltage	FO-GND (L) terminal	V_{FO}	20	V
	Fault Output Current	FO sink current	I_{FO}	14	mA
Module	Operating Temperature	—	TC	−20~+100	°C
	Storage Temperature Range	—	T_{stg}	−40~+125	°C
	Isolation Voltage	AC 1 minute	V_{ISO}	2500	V
	Screw Torque	M5	—	3	Nm

ELECTRICAL CHARACTERISTICS (T_j = 25°C)

a. Inverter stage

CHARACTERISTIC	SYMBOL	TEST CONDITION		MIN.	TYP.	MAX.	UNIT
Collector Cut-Off Current	I_{CEX}	V_{CEX} = 600 V	T_j = 25°C	—	—	1	mA
			T_j = 125°C	—	—	20	
Collector-Emitter Saturation Voltage	$V_{CE\ (sat)}$	V_D = 15 V, I_C = 75 A V_{IN} = 15 V → 0 V	T_j = 25°C	—	2.0	2.5	V
			T_j = 125°C	—	2.0	—	
Forward Voltage	V_F	I_F = 75 A		—	2.1	3.0	V
Switching Time	t_{on}	V_{CC} = 300 V, I_C = 75 A V_D = 15 V, V_{IN} = 15 V ↔ 0 V Inductive load (Note 1)		—	1.0	2.0	μs
	t_{off}			—	1.2	3.0	
	t_f			—	0.2	0.5	
	t_{rr}			—	0.1	0.3	

b. Control stage (T_j = 25°C)

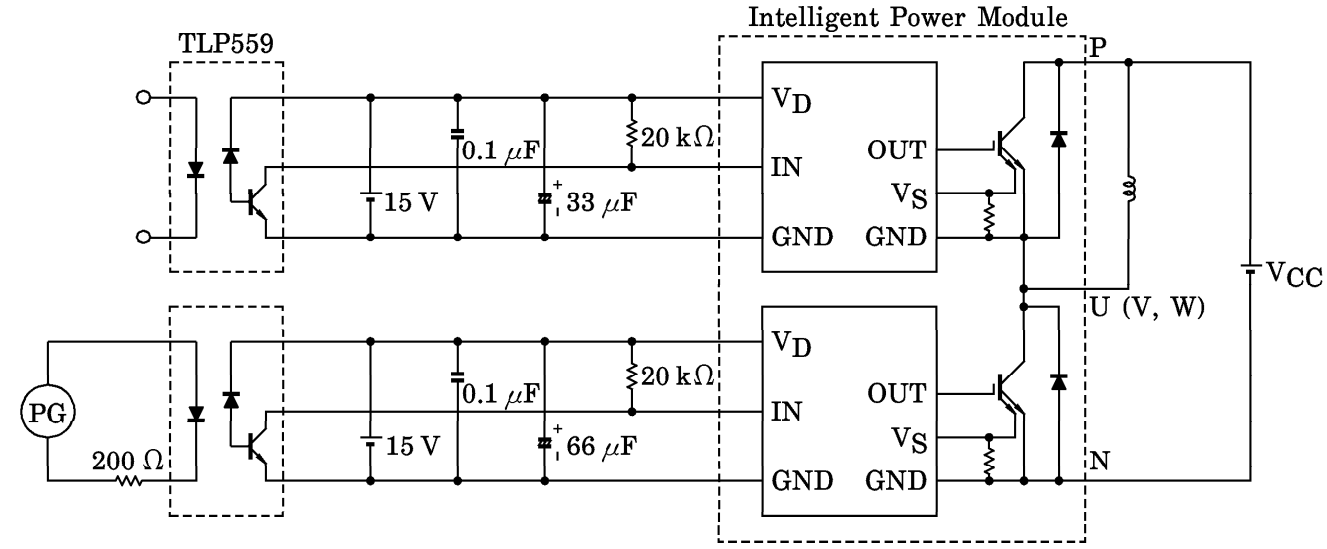
CHARACTERISTIC		SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Control Circuit Current	High Side	$I_{D\,(H)}$	V_D = 15 V	—	8	—	mA
	Low Side	$I_{D\,(L)}$		—	24	—	
Input-On Signal Voltage		$V_{IN\,(on)}$	V_D = 15 V, I_C = 75 mA	1.3	1.5	1.7	V
Input-Off Signal Voltage		$V_{IN\,(off)}$	V_D = 15 V, I_C = 75 mA	2.2	2.5	2.8	V
Fault Output Current	Protection	$I_{FO\,(on)}$	V_D = 15 V	8	10	12	mA
	Normal	$I_{FO\,(off)}$		—	—	1	
Over Current Protection Trip Level	Inverter	OC	V_D = 15 V, T_j = 125°C	105	150	—	A
Short Circuit Protection Trip Level	Inverter	SC	V_D = 15 V, T_j = 125°C	157	225	—	A
Over Current Cut-Off Time		$t_{off\,(OC)}$	V_D = 15 V	—	5	—	μs
Over Temperature Protection	Trip Level	OT	Case temperature	110	118	125	°C
	Reset Level	OTr		—	98	—	
Control Supply Under Voltage Protection	Trip Level	UV	—	11.0	12.0	12.5	V
	Reset Level	UVr		—	12.5	—	
Fault Output Pulse Width		t_{FO}	V_D = 15 V	1	2	3	ms

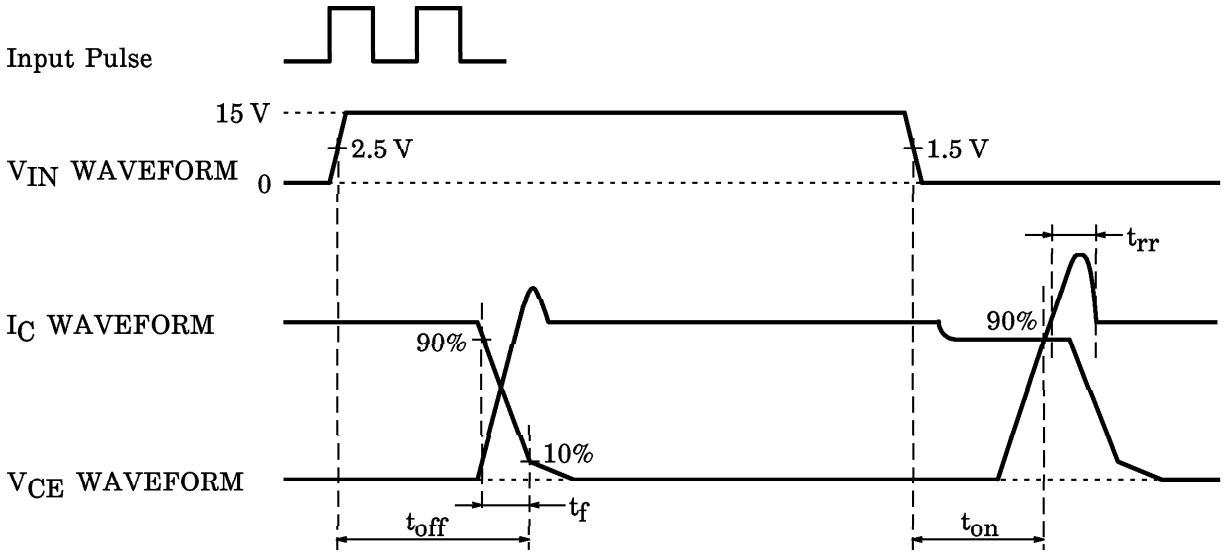
(*1) : Duty = 50%
(*2) : Duty = 50% (All Elements) & Fault Output Current (Sink)

d. Thermal resistance (T_j = 25°C)

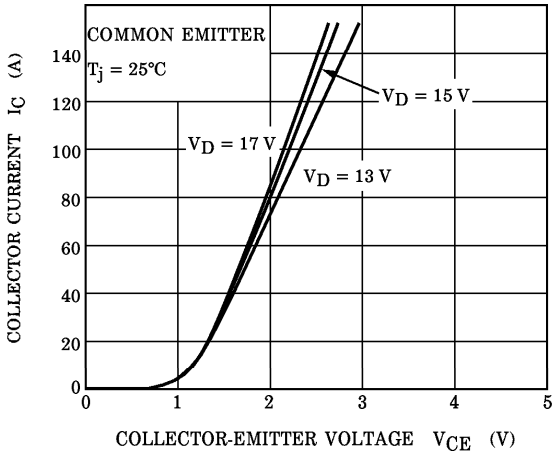
CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Junction to Case Thermal Resistance	$R_{th\ (j-c)}$	Inverter IGBT stage	—	—	0.553	°C / W
		Inverter FRD stage	—	—	1.000	
		—	—	—	—	
		—	—	—	—	
Case to Fin Thermal Resistance	$R_{th\ (c-f)}$	Compound is applied	—	0.05	—	°C / W

Note 1 : Switching time test circuit & timing chart

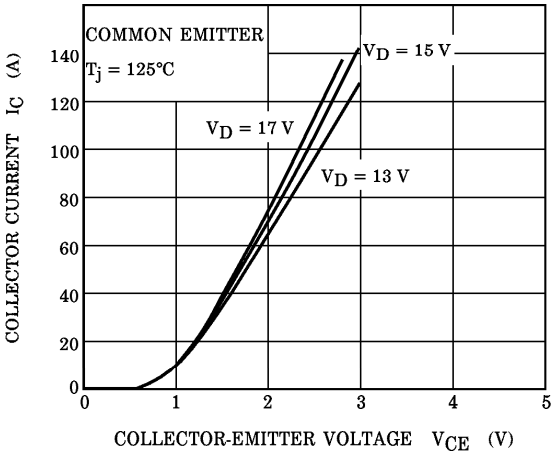




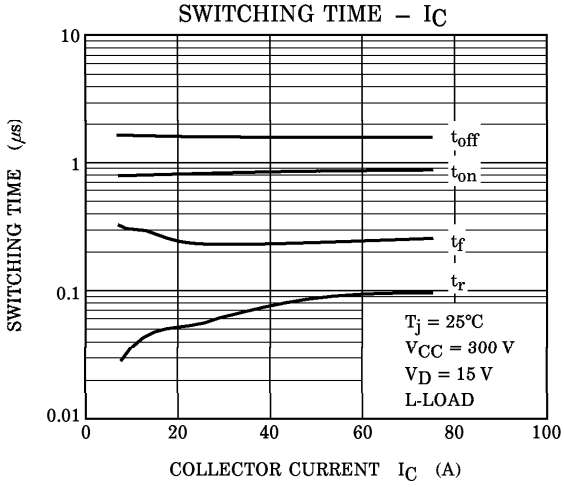
I_C – V_{CE}



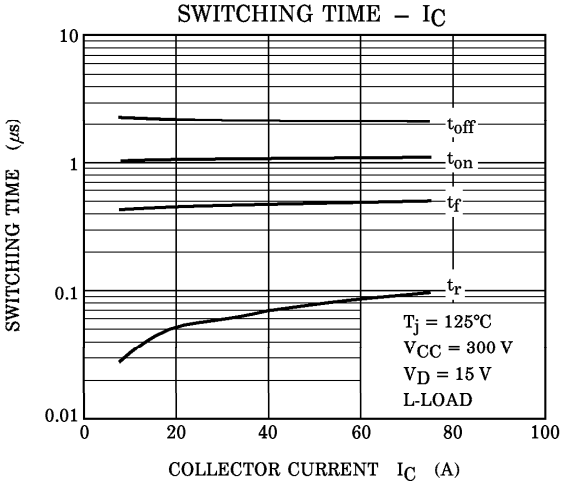
I_C – V_{CE}



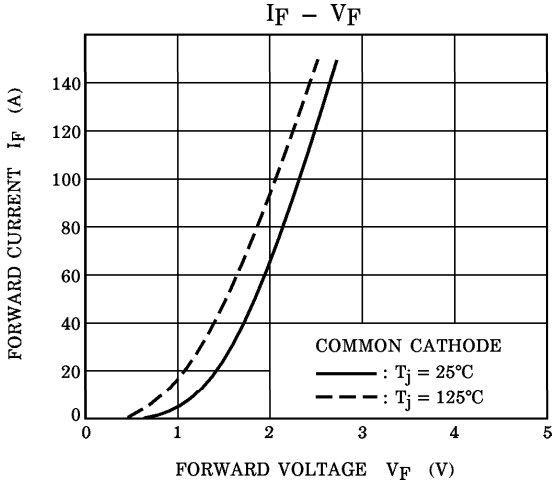
SWITCHING TIME – I_C



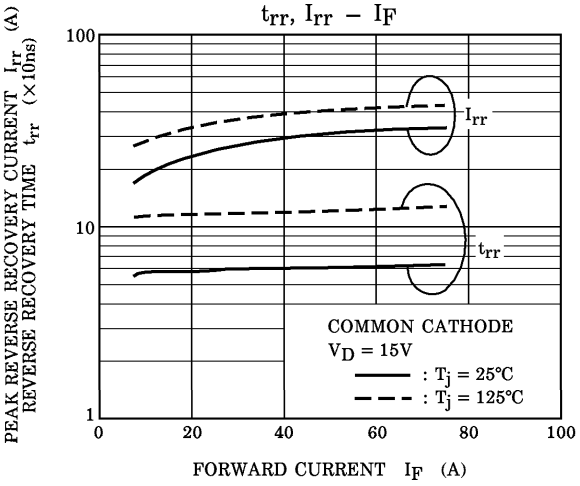
SWITCHING TIME – I_C



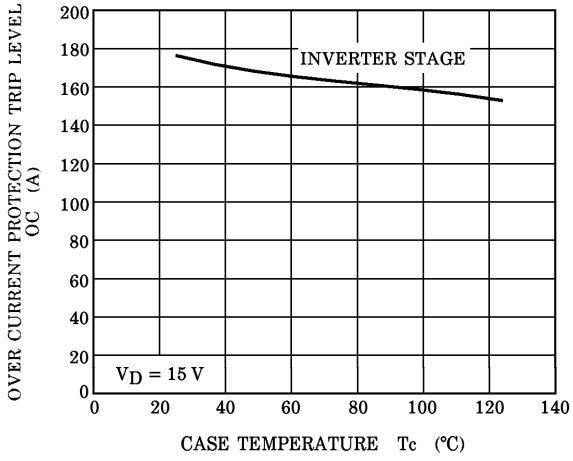
I_F – V_F



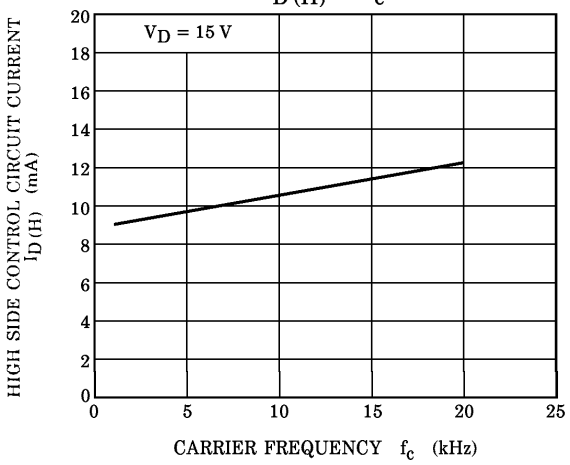
t_{rr}, I_{rr} – I_F



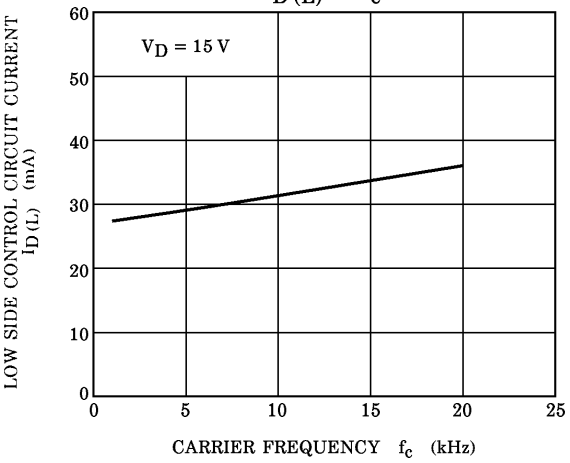
OC – Tc



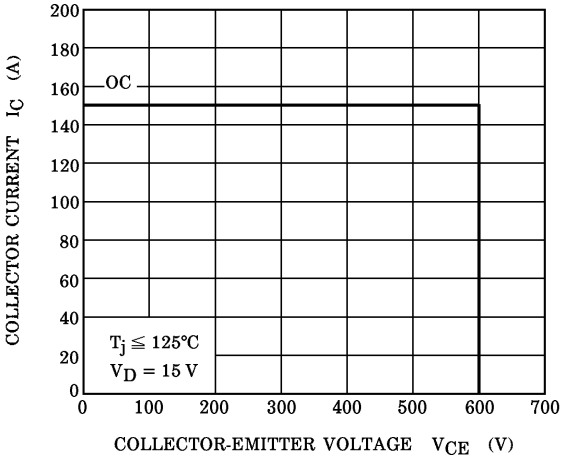
$I_{D(H)}$ – f_c



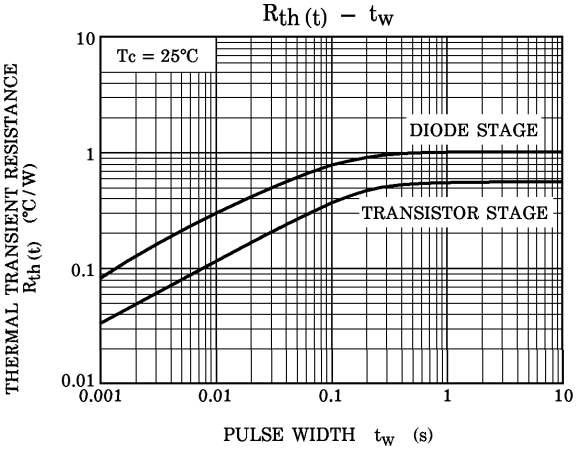
$I_{D(L)}$ – f_c



REVERSE BIAS SOA

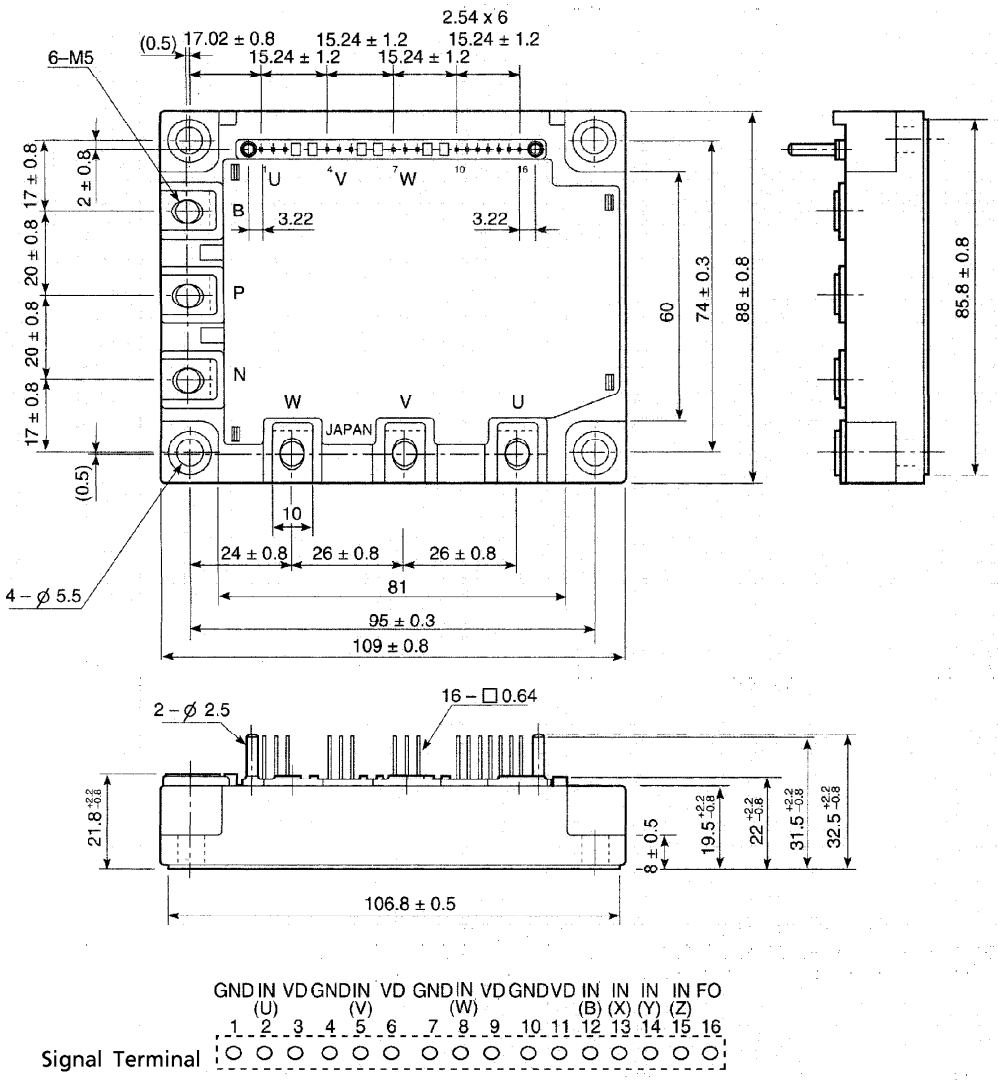


$R_{th(t)}$ – t_w



OUTLINE

Unit : mm



Signal Terminal

GND	IN (U)	VD	GND	IN (V)	VD	GND	IN (W)	VD	GND	VD	IN (B)	IN (X)	IN (Y)	IN (Z)	FO
1	2	3	4	5	6	7	8	9	10	11	12	13	14	15	16